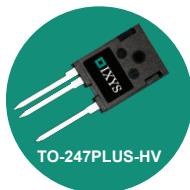


# 3600V Reverse Conducting IGBTs (BiMOSFETs™)

## Well-suited for high-voltage, high-current power conversion applications

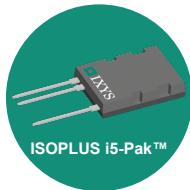
### FEATURES

- "Free" intrinsic body diode
- High power density
- High frequency operation
- Low conduction losses
- MOS gate turn on for drive simplicity
- 4000V electrical isolation



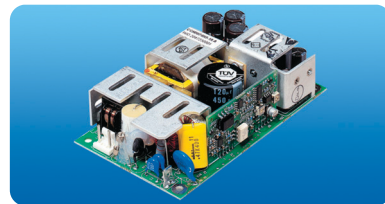
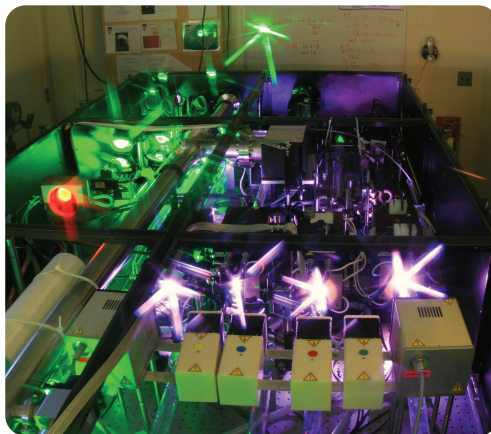
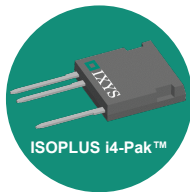
### ADVANTAGES

- Low gate drive requirements
- Space savings (eliminates multiple series-parallel lower voltage, lower current rated devices)
- Easy to mount



### APPLICATIONS

- Switched-mode and resonant-mode power supplies
- Uninterruptible Power Supplies (UPS)
- Laser and X-ray generators
- Capacitor discharge circuits
- High voltage pulser circuits
- High voltage test equipment



Part Number	$V_{CES}$ (V)	$I_{C25}$ $T_c=25^\circ\text{C}$ (A)	$I_{C110}$ $T_c=110^\circ\text{C}$ (A)	$V_{CE(sat)}$ typ. $T_j=25^\circ\text{C}$ (V)	$Q_{g(on)}$ typ. (nC)	$t_r$ (resistive load) typ. $T_j=25^\circ\text{C}$ (ns)	$V_f$ max. $T_j=25^\circ\text{C}$ (V)	$R_{th(jc)}$ max. ( $^\circ\text{C}/\text{W}$ )	Package
IXBF20N360	3600	45	18	2.9	110	1045	3.5	0.54	ISOPLUS i4-Pak™
IXBF50N360	3600	70	28	2.4	210	1750	3	0.43	ISOPLUS i4-Pak™
IXBL60N360	3600	92	36	2.8	450	910	5	0.3	ISOPLUS i5-Pak™
IXBX50N360HV	3600	125	50	2.4	210	1750	3	0.19	TO-247PLUS-HV

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Efficiency Through Technology

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